OP550, OP552, OP555, OP560, OP750 Series



Features:

- Wide receiving angle
- · Four sensitivity ranges
- Side-looking package
- Ideal for space-limited applications
- Ideal for PCBoard mounting
- Choice of clear, opaque or blue-tinted package



Description:

OP550, OP552, OP555 and OP750 series consists of a NPN silicon phototransistor molded in an epoxy package with a wide receiving angle that provides relatively even reception over a large area. The **OP750** series have additional circuitry to enhance the operation of the device for stray light levels.

The **OP560** series consists of a NPN silicon photodarlington transistor molded in an epoxy package with a wide receiving angle that provides relatively even reception over a large area.

The side-looking package design allows easy PCBoard mounting of slotted optical switches or optical interrupt detectors.

The OP550, OP560 and OP750 devices have an external lens in a clear epoxy package.

The **OP552** device has an integral lens in an opaque plastic package that is optically transparent to infrared light but opaque to visible wavelengths. This feature allows the device to be used under high ambient light conditions—or anywhere external light sources could interfere with the intended sensing application (visible light immunity).

The **OP555** device has an internal lens in a blue-tinted package. The lensing effect of this package allows an acceptance half-angle of 28° when measured from the optical axis to the half-power point.

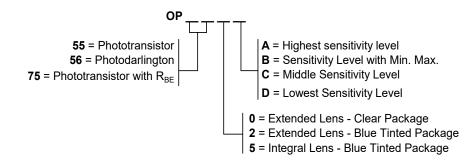
These devices are 100% production tested using infrared light for close correlation with OPTEK's GaAs and GaAlAs emitters. All of these sensors are mechanically and spectrally matched to the **OP140, OP142, OP145, OP240** and **OP245** series of infrared emitting diodes.

<u>Please refer to Application Bulletins 208 and 210 for additional design information and reliability (degradation) data.</u> For custom versions please contact your OPTEK representative.

Applications:

- Applications requiring wide receiving angle
- Applications requiring PCBoard mounting
- Space-limited applications
- Optical switches
- Optical interrupt detectors
- Optical encoders
- Non-contact position sensing
- Machine automation



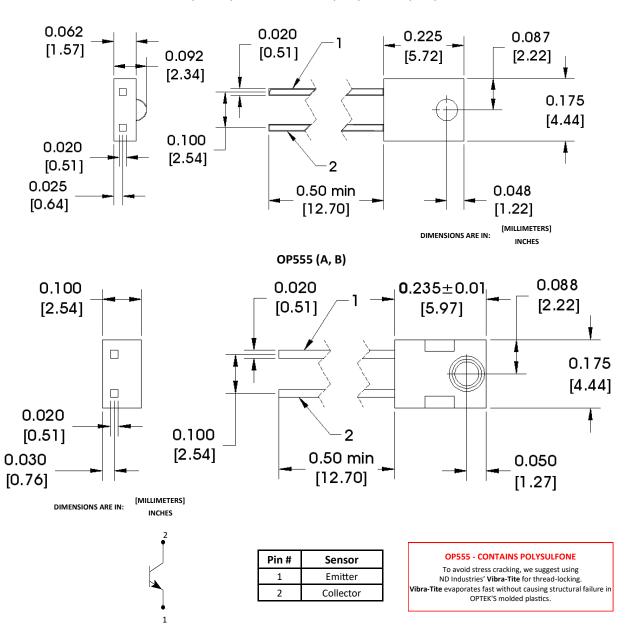


Available Part Numbers							
OP550A	OP552D	OP560A	OP750A				
OP550B	OP555A	OP560C	OP750B				
OP550C	OP555B	OP565B (Obsolete)	OP750D (Obsolete)				
OP550D (Obsolete)	OP555C (Obsolete)		OP770A (Obsolete)				





OP550 (A, B, C), OP552D, OP560 (A, C), OP750 (A, B)



Notes:

- 1. RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering. A maximum 20 grams force may be applied to the leads when soldering.
- 2. For OP550, OP560 and OP555, derate linearly 1.33 mW/° C above 25° C. For OP552, derate linearly 1.25 mW/° C above 25° C.
- For all phototransistors in this series, the light source is an unfiltered GaAs LED with a peak emission wavelength of 935 nm. For OP550 and OP555 only, a radiometric intensity level that varies less than 10% over the entire lens surface of the phototransistor being tested applies.
- 4. To calculate typical collector dark current in μ A, use the formula $I_{CEO}=10^{\frac{(0.040\,T_A-3.4)}{A}}$, where T_A is ambient temperature in ° C.

Rev C 05/2022 Page 2





Electrical Specifications

Absolute Maximum Ratings (T_A = 25° C unless otherwise noted)

Storage Temperature Range	-40° C to +100° C
Operating Temperature Range	
OP550, OP555, OP560, OP750	-40° C to +100° C
OP552	-40° C to +85° C
Collector-Emitter Voltage	30 V
Emitter-Collector Voltage	5 V
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 seconds with soldering iron]	260° C ⁽¹⁾
Power Dissipation	
OP550, OP552, OP555, OP560	100 mW ⁽²⁾
OP750	200 mW ⁽²⁾

Rev C 05/2022 Page 3





Electrical Specifications

Electrical Characteristics (T_A = 25° C unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
I _{C(ON)}	On-State Collector Current OP550A, OP555A OP550B, OP555B OP550C OP552D	2.55 1.30 0.25 0.25	- - -	- 4.70 2.40 -	mA .	$V_{CE} = 5.0 \text{ V}, E_E = 1.0 \text{ mW/cm}^{2(3)}$
	OP560A OP560C	6.6 1.1	-	-		V _{CE} = 2.0 V, E _E = 0.1 mW/cm ²⁽³⁾
	OP750A OP750B	2.25 1.50	-	7.00 4.20		V _{CE} = 5.0 V, E _E = 1.0 mW/cm ²⁽³⁾
I _C /Δ T	Relative I _C Charge with Temperature	-	1.00	-	%/° C	$V_{CE} = 5.0 \text{ V}, E_E = 1.0 \text{ mW/cm}^2,$ $\lambda = 935 \text{ nm}$
I _{CEO}	Collector-Dark Current	-	-	100	nA	$V_{CE} = 10.0 \text{ V}, E_E = 0^{(4)}$
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage OP550, OP552, OP555, OP750 OP560	30 15	-	-	V	$I_C = 100 \mu A, E_E = 0^{(4)}$ $I_C = 1 mA, E_E = 0^{(4)}$
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage	5.0	-	-	V	Ι _Ε = 100 μΑ
V _{CE(SAT)}	Collector-Emitter Saturation Voltage OP550, OP552, OP555, OP750 OP560	-	-	0.40 1.10	V	$I_C = 100 \mu A, E_E = 1.0 \text{ mW/cm}^{2(3)}$ $I_C = 0.4 \text{ mA}, E_E = 0.1 \text{ mW/cm}^{2(3)}$

See page 2 for Notes

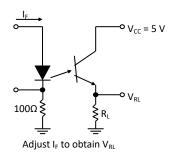
Rev C 05/2022 Page 4



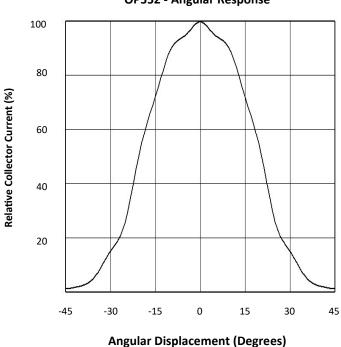


Performance

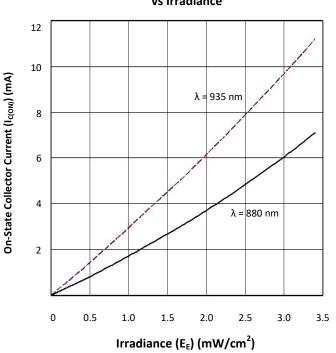
Switching Test Circuit



OP552 - Angular Response



OP552 - On-State Collector Current vs Irradiance







Performance

OP552 - Output Vs Frequency

80

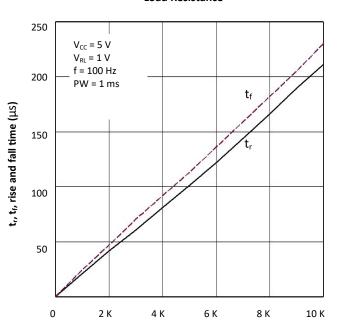
R_i = 10 K

R_i = 1 K

20

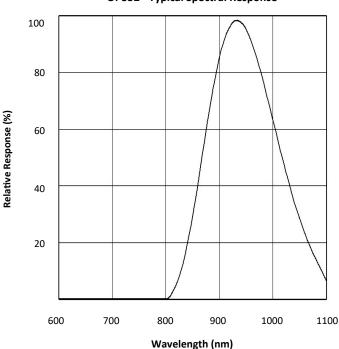
1 10 100 1000

OP552 - Rise and Fall Time vs Load Resistance



OP552 - Typical Spectral Response

Frequency (KHz)



Load Resistance (Ohms) OP552 - Coupling Characteristic

